

# TPEG<sup>™</sup> MEMS RF+ Technology for Vertical Probe Heads



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### Outline

#### Introduction

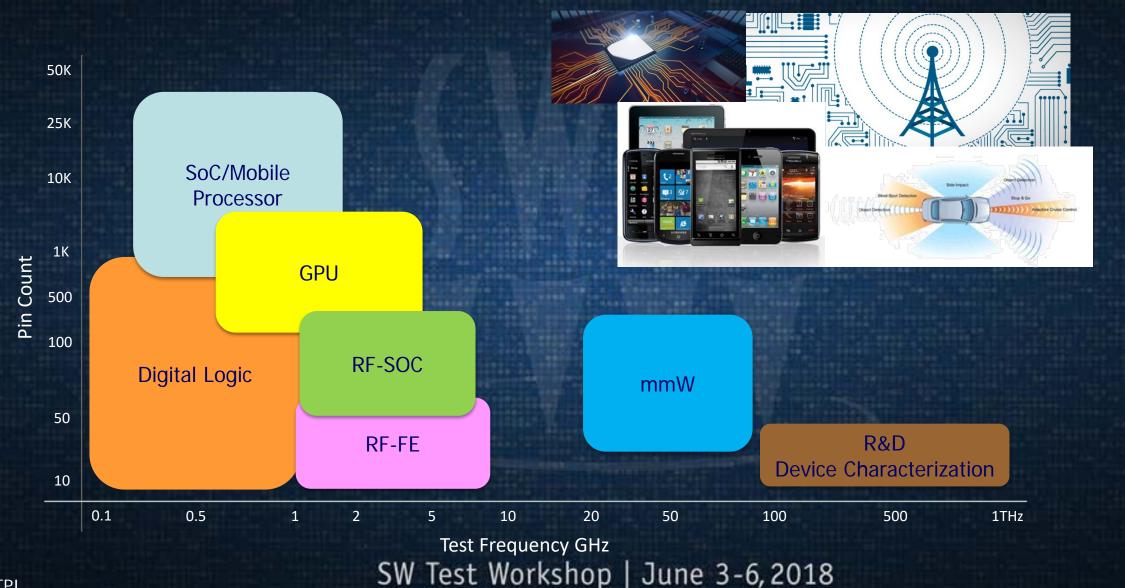
- Technoprobe TPEG<sup>™</sup> RF+ architecture
- Production test vehicle
- Modeling data
- Internal experimental validation data
- Conclusions
- Future work

# Introduction

#### • Standard vertical probe heads do not have satisfactory RF properties.

- On the other hand, they offer a series of advantages over other typical RF technologies based on flexible membranes.
- Technoprobe developed a new PH architecture that provides excellent RF properties based on TPEG<sup>™</sup> MEMS vertical PH technology.
  - This technology improves the return loss (RL), the insertion loss (IL), as well as the other RF related specs.....up to 10 GHz
  - The enhanced RF performances are obtained thanks to additional GND paths inside the PH connected both to the GND of the device and to the space transformer, to control signal impedance

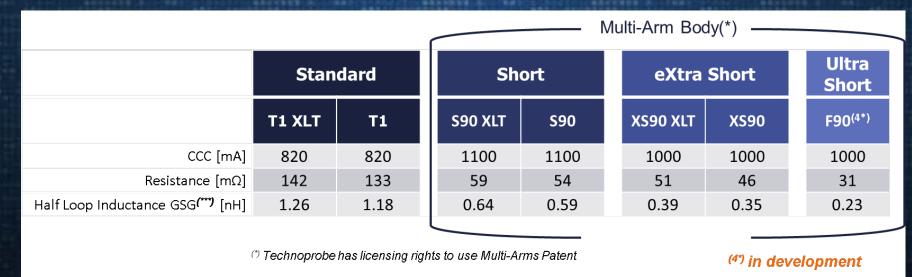
# **PC Market Segments : High Speed and RF**



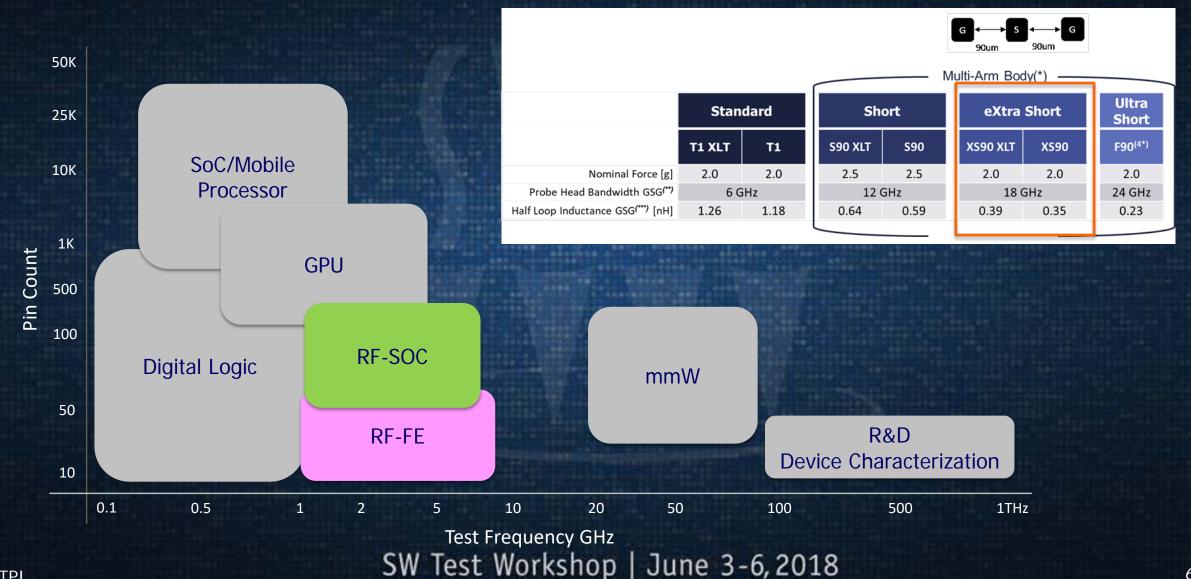
# **Probes: High Speed Challenges**

#### • Challenges:

- Probe cards struggle between having a long needle to optimize the mechanical performance and a short needle to optimize the frequency performances
- Shorter needles will generate higher forces than ideal
- Technoprobe Solution: Vertical MEMS Probe Head
  - Multi-arm needle body allows shorter needles and maintains standard forces



# **RF-SOC and RF Front End: Available TP Technology**



# **TPEG™ RF architecture – Patent Pending**

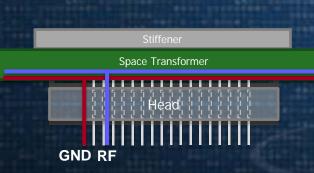
#### • Challenge:

 RF device layouts are not optimized for RF probing and often short needles are not enough to match RF performance required by customer's application

**RF** Architecture

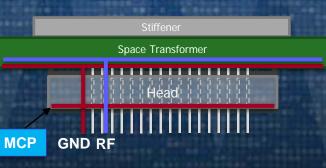
(Patent pending)

#### • Technoprobe Solution (RF and RF+):

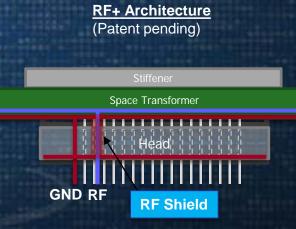


**Standard Architecture** 

 GND and RF Signals are not matched for all the length of the needles creating <u>not optimized</u> IL, RL and LI (Loop Inductance)



 GND plane is added closer to the DUT thru TP proprietary MCP technology (Multi-Conductive-Plates) optimizing GND noise and LI



Shield is created around RF signals inside the head using TP proprietary SRF technology (Shield-RF) optimizing IL, RL, LI and GND noise

## **Production test vehicle**

#### • Device

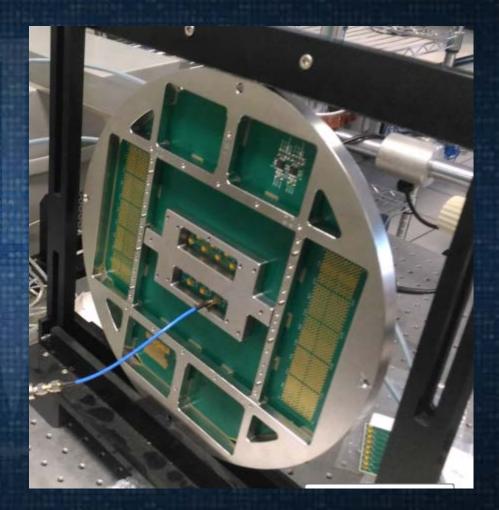
- SAW filter
- Pitch is 370 μm and uses minimal grounding
- 4 pins / DUT: IN, OUT and 2x GND
- Probe card
  - Probing x8 diagonal pattern

#### Tester platform

UltraFLEX 300mm with RF interface (LEGO block)

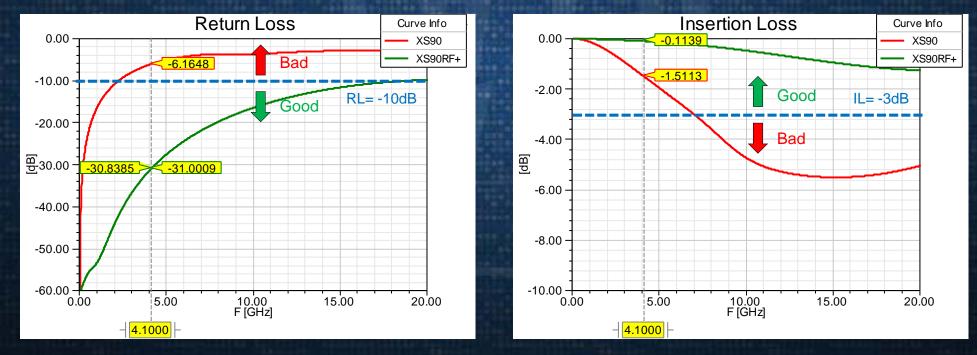
#### • **RF requirement**

 Required filter response mask given by customer



#### Modeling Data PH only

- RF+ architecture based on TPEG<sup>™</sup> MEMS XS90 probing technology allows to improve frequency performances
- FEM 3D simulation of standalone probe head was performed:
  - Both return loss and insertion loss show significant improvement
  - Filter response is in spec with respect to customer proprietary filter s-parameter model



# **Experimental data**

- Three different experimental setups have been used
- RF characterization
  - RL and IL measured with test fixture and VNA up to 20 GHz
- DC tests with dedicated wired space transformer
  - DC continuity test with prober
  - Leakage test on probe card analyser

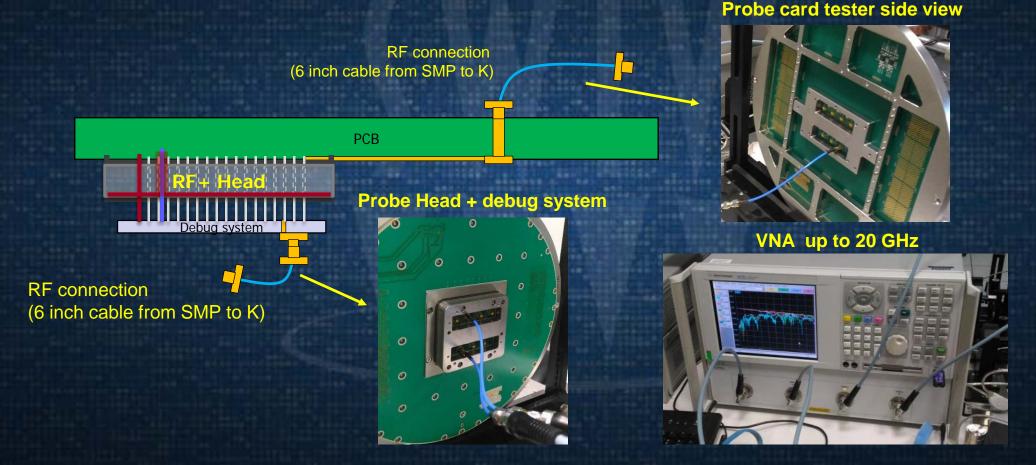
#### RF tests on prober

 Probe card was tested on customer wafer filter (Filter shape under IP no sharable results)

# **RF Characterization**

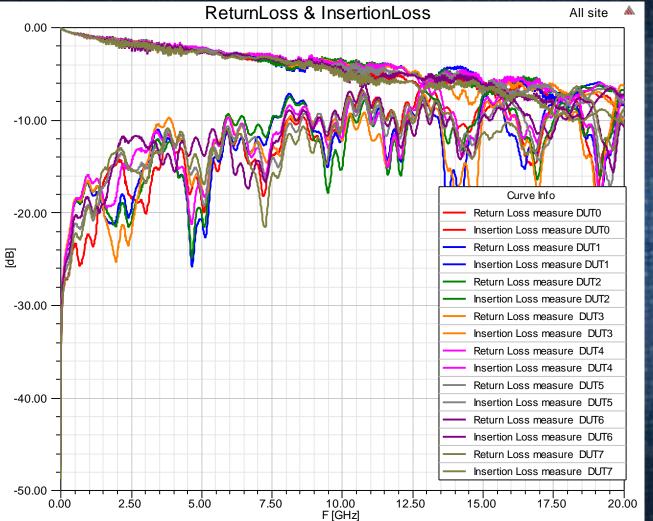
**Experimental setup** 

#### Measure system fixture for RF+ architecture



### **RF** Characterization

#### **Experimental results: RL and IL**

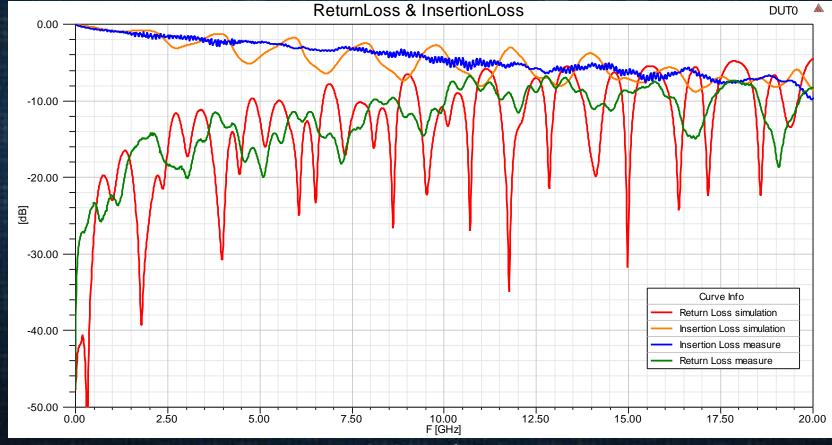


- All 8 sites show similar value of return loss and insertion loss
- Differences are given by PCB design
- Maximum working frequency is 8 GHz because of PCB design: filter device have to work DC to about 5 GHz
- From simulation with higher performance PCB, RF+ architecture is able to work up to 10 GHz (or more)

### **RF Characterization**

**Experimental vs. Simulation results** 

 Comparison between simulated and measured results allowed to validate the consistency of 3D FEM simulation models

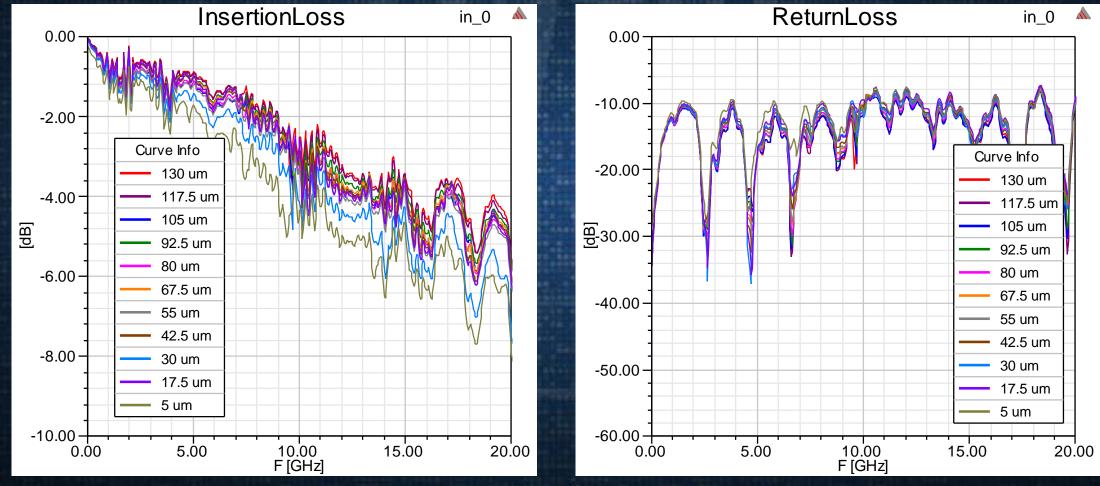


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### **RF characterization**

#### IL and RL varying working overdrive

#### • Characterization with different overdrive: technology shows low sensitivity to working OD



### Space Transformer DC Tests Experimental setup



 Dedicated wired space transformer designed and manufactured • Probe card loaded on Accretech **UF3000EX** prober Blank wafers used to measure Path Resistance by means of **Keithley Kelvin equipment** 

**Space Transformer DC Tests** DC continuity test between GND and shield

 Path Resistance tests were performed to measure the electrical continuity between GND probes and metallic shield inside the PH while probing on a nonconductive silicon wafer

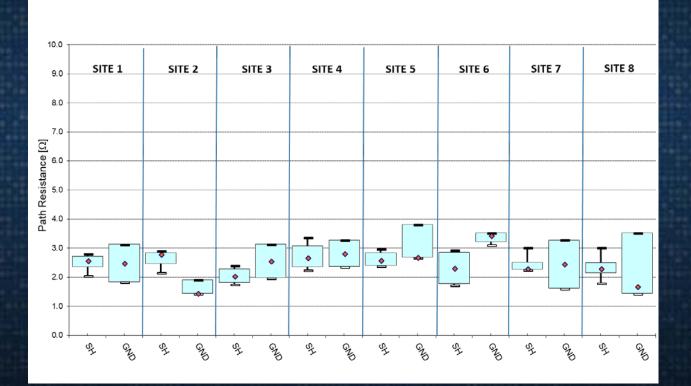
 Next slides are show Path Resistance test results in function of PH site and of working OD

### Space Transformer DC Tests

Path Resistance results in function of PH site

#### Path Resistance tests in function of PH site at a fixed working OD (75 μm)

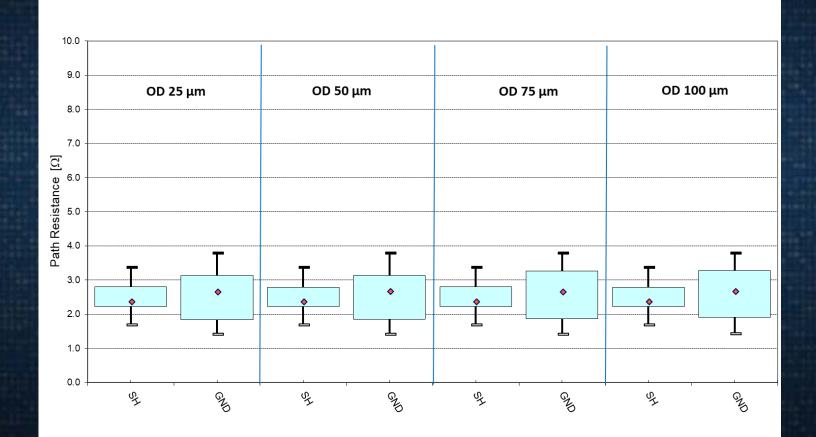
Results are stable and comparable



### **Space Transformer DC Tests**

Path Resistance results varying working OD

#### Good Path Resistance stability observed in the whole working OD range:



### **Space Transformer DC Tests**

Leakage test on probe card analyzer

- Leakage tests were performed on Rudolph PRVX4 probe card analyzer
- No shorts have been detected in the whole working OD range
- Leakage measurements were below 0.12 nA @ 5 V (vs. 10 nA ref spec)



## **RF Tests on Prober**

**Experimental setup** 

 RF+ architecture has been validated on the prober using customer wafer and VNA up to 20 GHz to measure filter + probe card response



### **RF Tests on Prober**

**Experimental results on Customer wafer** 

• On all 8 sites, we were able to measure filter shape compliant with required mask at different working OD

Site Number	Test @50 OD	Test @75 OD	Test @100 OD
Site 1	PASS	PASS	PASS
Site 2	PASS	PASS	PASS
Site 3	PASS	PASS	PASS
Site 4	PASS	PASS	PASS
Site 5	PASS	PASS	PASS
Site 6	PASS	PASS	PASS
Site 7	PASS	PASS	PASS
Site 8	PASS	PASS	PASS

### Conclusions

- RF+ architecture is able to combine good frequency performance with the advantages of TPEG<sup>™</sup> MEMS vertical technology
  - High parallelism
  - Pin to pin onsite reparability
  - Low pad damage
- RF results aligned with model
- Ready for on onsite test

### **Future work**

#### • Evaluate feasibility of:

- More complex device
- Higher parallelism

 Probe head technology has the same powerful of standard vertical technology into manage device complexity... Need to understand space transformer capability into deal with high number of RF pins

# **Thanks for your Support !**

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